Abstract

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monolithically integrated optic triplexer described herein that can be mounted in one transistor outline (TO) can and can be used in a passive optical The monolithically integrated optic triplexer network. emitting laser that is capable (1) an includes: transmitting a 1310 +/-10nm optical signal; (2) a first photodiode that is capable of receiving a 1490 +/-5nm optical signal; and (3) a second photodiode that is capable of receiving a 1550 +/-5nm optical signal. In one embodiment, the emitting laser is placed on top of the two are monolithically integrated on a which photodiodes And in another embodiment, the emitting laser substrate. and two photodiodes are all monolithically integrated on a The monolithically integrated optic triplexer substrate. may also include a thin film filter that is located between the emitting laser and the first photodiode. In addition, the monolithically integrated optic triplexer may include a film filter that is located between the Also described photodiode and the second photodiode. herein is a method for making the monolithically integrated optic triplexer.